

# NTMD6P02R2

Preferred Device

## Power MOSFET 6 Amps, 20 Volts P-Channel SOIC-8, Dual

### Features

- Ultra Low  $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual SOIC-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- SOIC-8 Mounting Information Provided
- Pb-Free Packages are Available

### Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	-20	V
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 12$	V
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	$P_D$	2.0	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	$I_D$	-7.8	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	$I_D$	-5.7	A
Maximum Operating Power Dissipation	$P_D$	0.5	W
Maximum Operating Drain Current	$I_D$	-3.89	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-40	A
Thermal Resistance – Junction-to-Ambient (Note 2)	$R_{\theta JA}$	98	$^{\circ}\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	$P_D$	1.28	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	$I_D$	-6.2	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	$I_D$	-4.6	A
Maximum Operating Power Dissipation	$P_D$	0.3	W
Maximum Operating Drain Current	$I_D$	-3.01	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-35	A
Thermal Resistance – Junction-to-Ambient (Note 3)	$R_{\theta JA}$	166	$^{\circ}\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	$P_D$	0.75	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	$I_D$	-4.8	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	$I_D$	-3.5	A
Maximum Operating Power Dissipation	$P_D$	0.2	W
Maximum Operating Drain Current	$I_D$	-2.48	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-30	A
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^{\circ}\text{C}$ ( $V_{DD} = -20$ Vdc, $V_{GS} = -5.0$ Vdc, Peak $I_L = -5.0$ Apk, $L = 40$ mH, $R_G = 25$ $\Omega$ )	$E_{AS}$	500	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	$T_L$	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

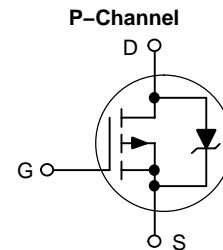
1. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided),  $t = 10$  seconds.
2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided),  $t =$  steady state.
3. Minimum FR-4 or G-10 PCB,  $t =$  steady state.
4. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2%.



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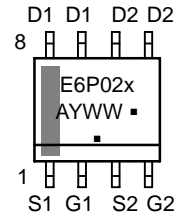
6 AMPERES, 20 VOLTS



### MARKING DIAGRAM & PIN ASSIGNMENT



SOIC-8  
CASE 751  
STYLE 11



E6P02 = Specific Device Code  
x = Blank or S  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTMD6P02R2	SOIC-8	2500 / Tape & Reel
NTMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NTMD6P02R2SG	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

Preferred devices are recommended choices for future use and best overall value.

# NTMD6P02R2

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)\*

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Positive)	V <sub>(BR)DSS</sub>	-20 -	- -11.6	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V <sub>DS</sub> = -20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 25°C) (V <sub>DS</sub> = -20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 70°C)	I <sub>DSS</sub>	- -	- -	-1.0 -5.0	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = -12 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	-100	nAdc
Gate-Body Leakage Current (V <sub>GS</sub> = +12 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	100	nAdc

### ON CHARACTERISTICS

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	-0.6 -	-0.88 2.6	-1.20 -	Vdc mV/°C
Static Drain-to-Source On-State Resistance (V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -6.2 Adc) (V <sub>GS</sub> = -2.5 Vdc, I <sub>D</sub> = -5.0 Adc) (V <sub>GS</sub> = -2.5 Vdc, I <sub>D</sub> = -3.1 Adc)	R <sub>DS(on)</sub>	- - -	0.027 0.038 0.038	0.033 0.050 -	Ω
Forward Transconductance (V <sub>DS</sub> = -10 Vdc, I <sub>D</sub> = -6.2 Adc)	g <sub>FS</sub>	-	15	-	Mhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>ISS</sub>	-	1380	1700	pF
Output Capacitance		C <sub>OSS</sub>	-	515	775	
Reverse Transfer Capacitance		C <sub>RSS</sub>	-	250	450	

### SWITCHING CHARACTERISTICS (Notes 5 and 6)

Turn-On Delay Time	(V <sub>DD</sub> = -10 Vdc, I <sub>D</sub> = -1.0 Adc, V <sub>GS</sub> = -10 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	15	25	ns
Rise Time		t <sub>r</sub>	-	20	50	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	85	125	
Fall Time		t <sub>f</sub>	-	50	110	
Turn-On Delay Time	(V <sub>DD</sub> = -16 Vdc, I <sub>D</sub> = -6.2 Adc, V <sub>GS</sub> = -4.5 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	17	-	ns
Rise Time		t <sub>r</sub>	-	65	-	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	50	-	
Fall Time		t <sub>f</sub>	-	80	-	
Total Gate Charge	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -6.2 Adc)	Q <sub>tot</sub>	-	20	35	nC
Gate-Source Charge		Q <sub>gs</sub>	-	4.0	-	
Gate-Drain Charge		Q <sub>gd</sub>	-	8.0	-	

### BODY-DRAIN DIODE RATINGS (Note 5)

Diode Forward On-Voltage	(I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	- -	-0.80 -0.65	-1.2 -	Vdc
Diode Forward On-Voltage	(I <sub>S</sub> = -6.2 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = -6.2 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	- -	-0.95 -0.80	- -	Vdc
Reverse Recovery Time	(I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc, dI <sub>S</sub> /dt = 100 A/μs)	t <sub>rr</sub>	-	50	80	ns
		t <sub>a</sub>	-	20	-	
		t <sub>r</sub>	-	30	-	
Reverse Recovery Stored Charge		Q <sub>RR</sub>	-	0.04	-	μC

5. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

6. Switching characteristics are independent of operating junction temperature.

\*Handling precautions to protect against electrostatic discharge are mandatory.

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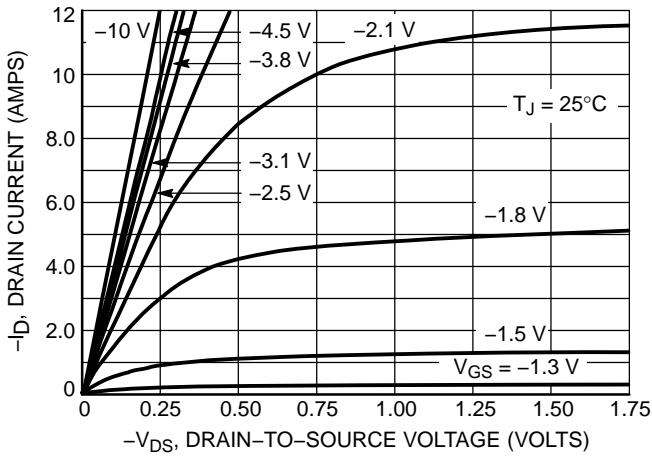


Figure 1. On-Region Characteristics

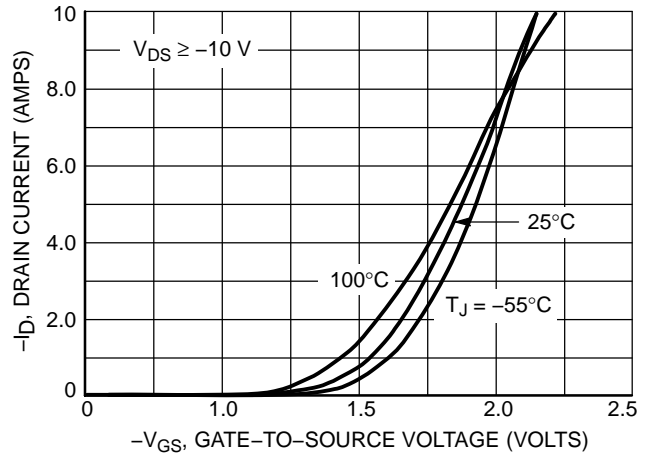


Figure 2. Transfer Characteristics

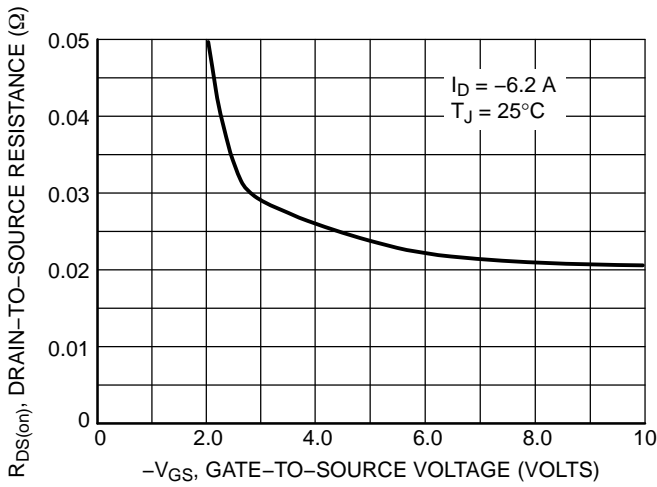


Figure 3. On-Resistance versus Gate-To-Source Voltage

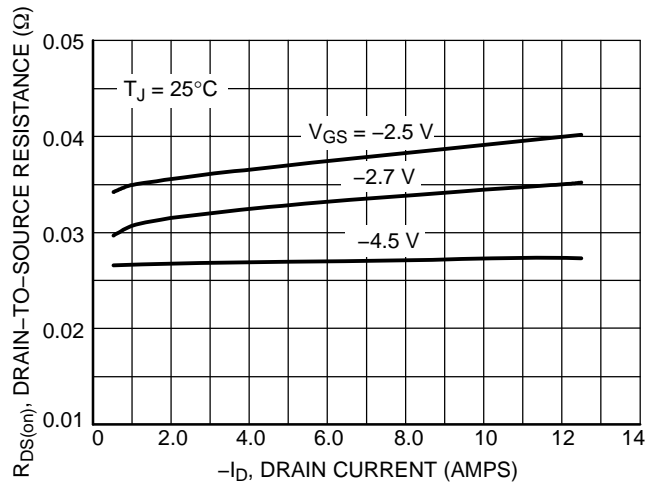


Figure 4. On-Resistance versus Drain Current and Gate Voltage

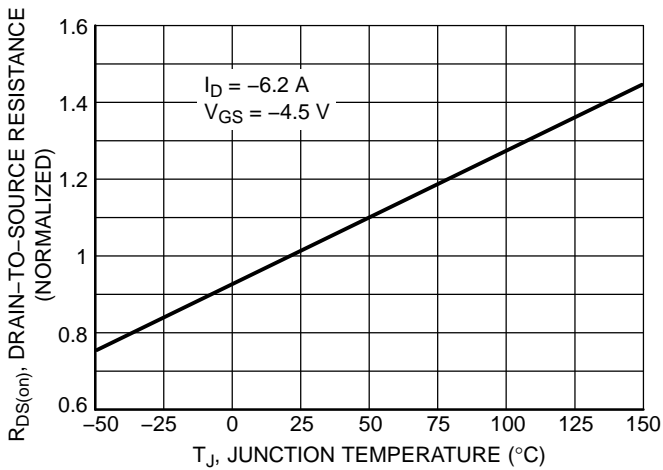


Figure 5. On-Resistance Variation with Temperature

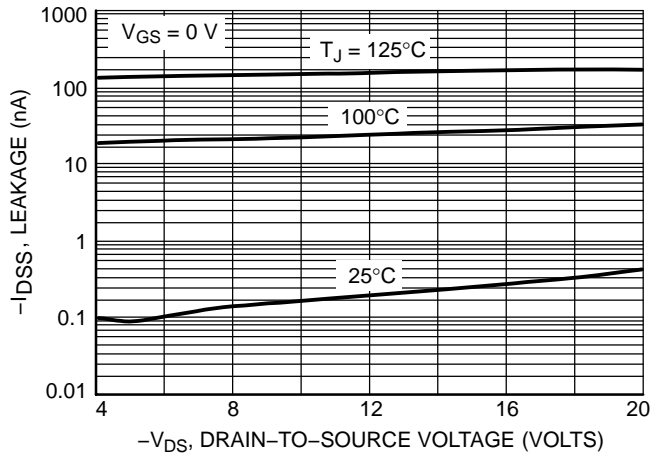
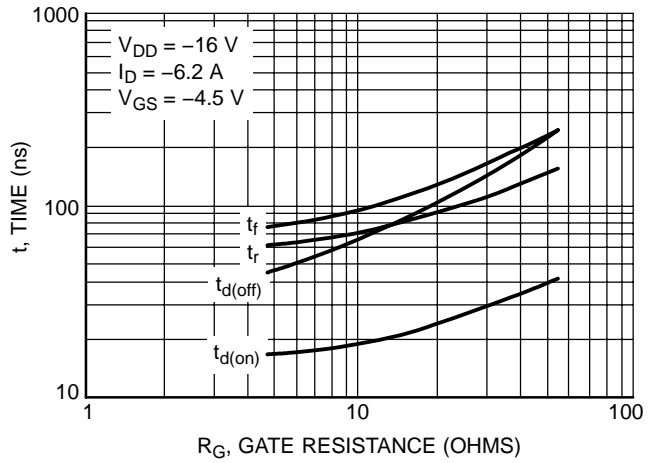
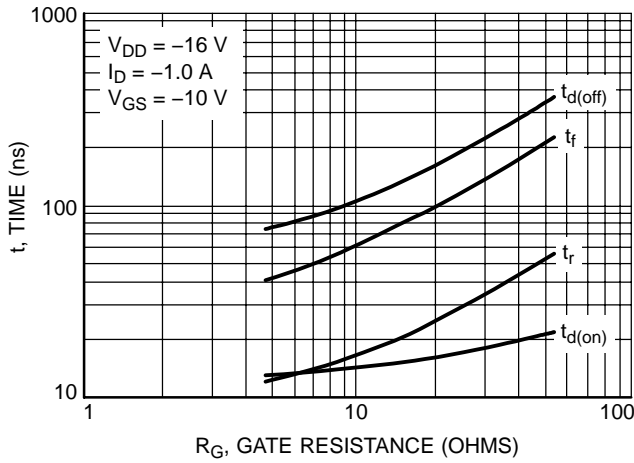
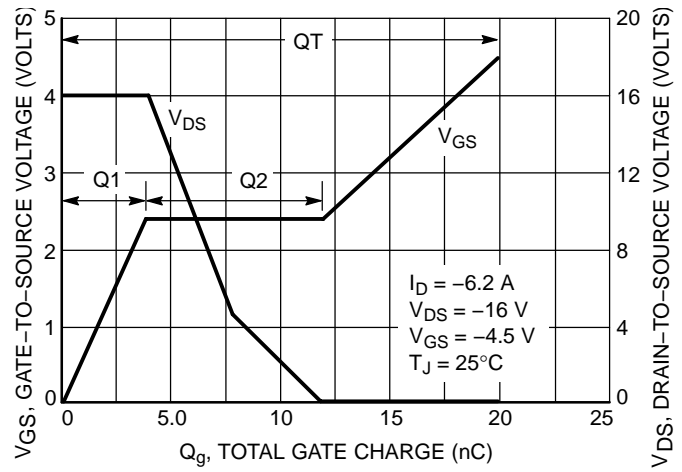
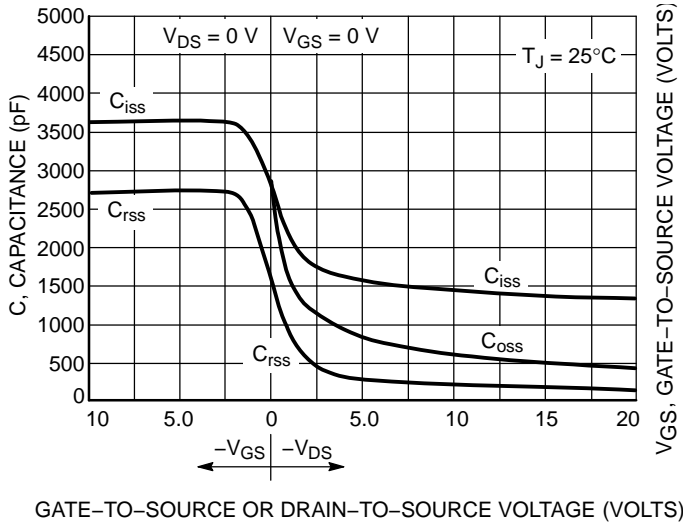
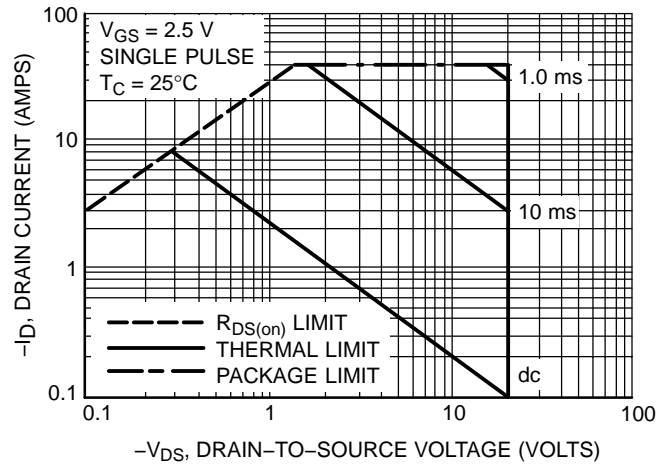
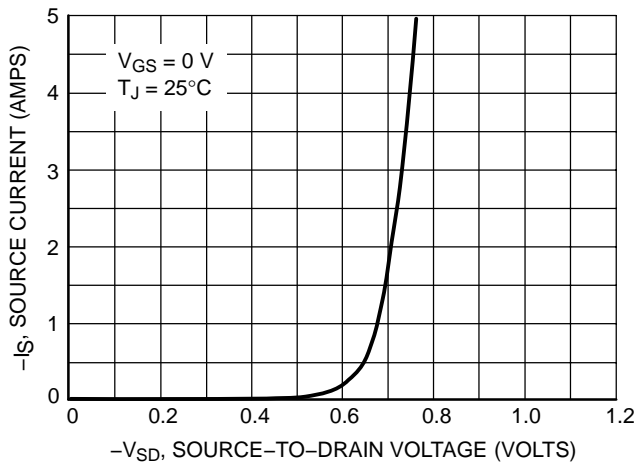


Figure 6. Drain-To-Source Leakage Current versus Voltage

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## DRAIN-TO-SOURCE DIODE CHARACTERISTICS



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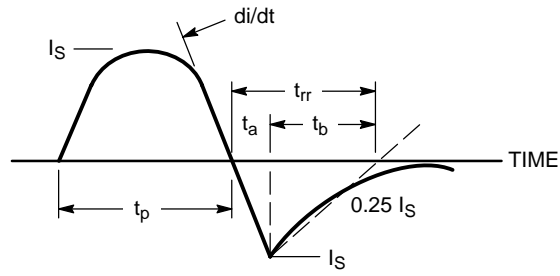


Figure 13. Diode Reverse Recovery Waveform

## TYPICAL ELECTRICAL CHARACTERISTICS

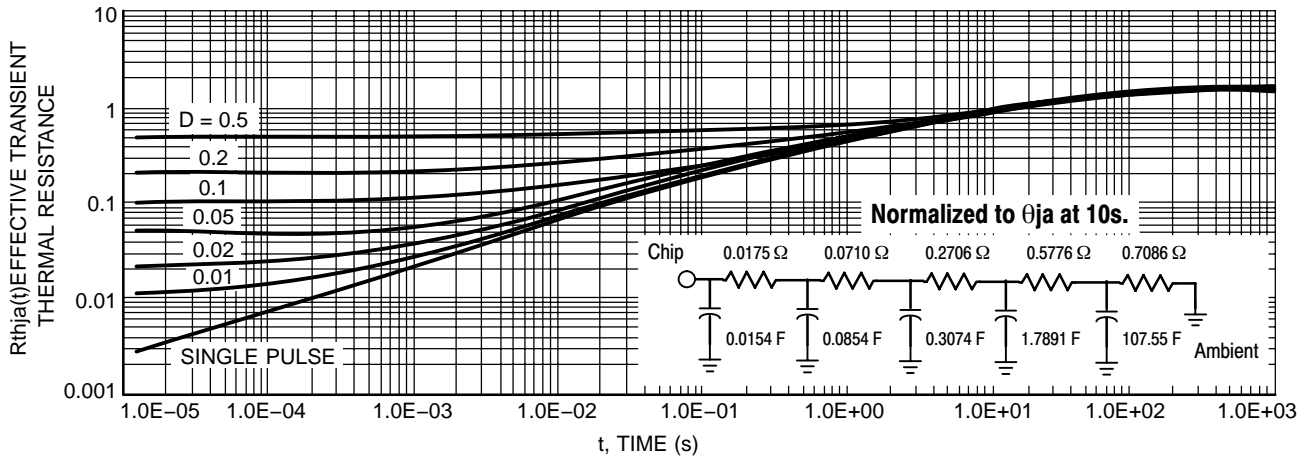
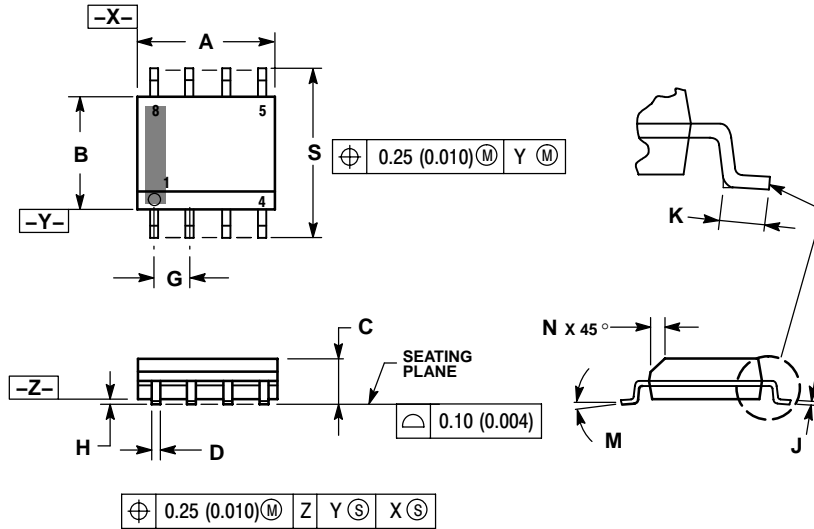


Figure 14. Thermal Response

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## PACKAGE DIMENSIONS

SOIC-8 NB  
CASE 751-07  
ISSUE AH

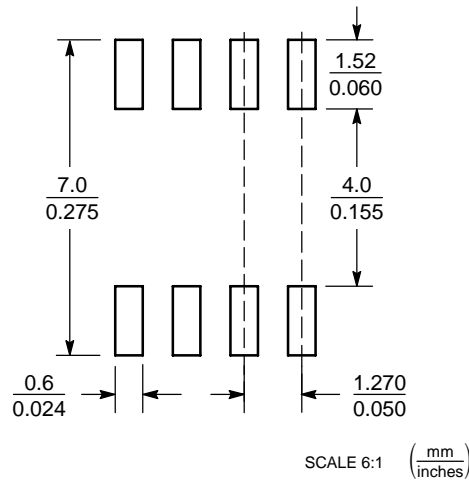


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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